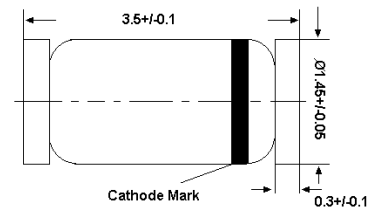


LL4148

Silicon Epitaxial Planar Switching Diode

Fast switching diode in MiniMELF case especially suited for automatic surface mounting

LL-34



Glass case MiniMELF
Dimensions in mm

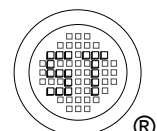
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

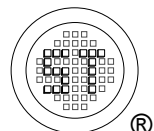
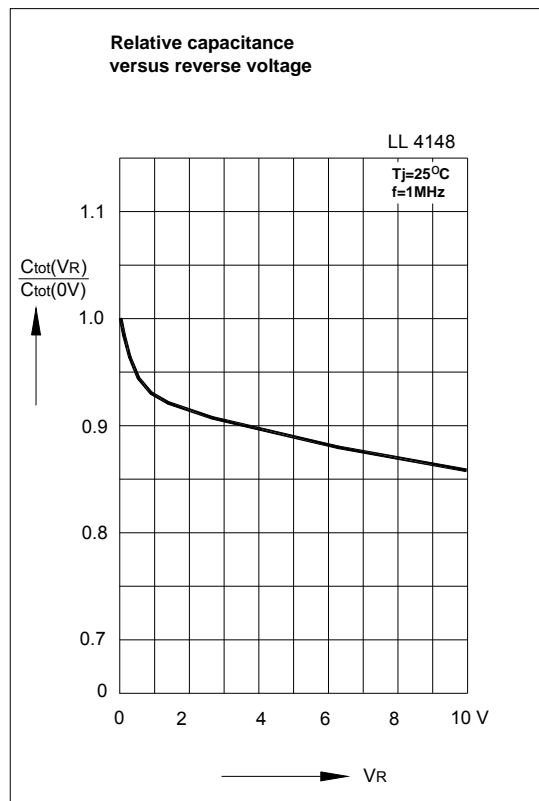
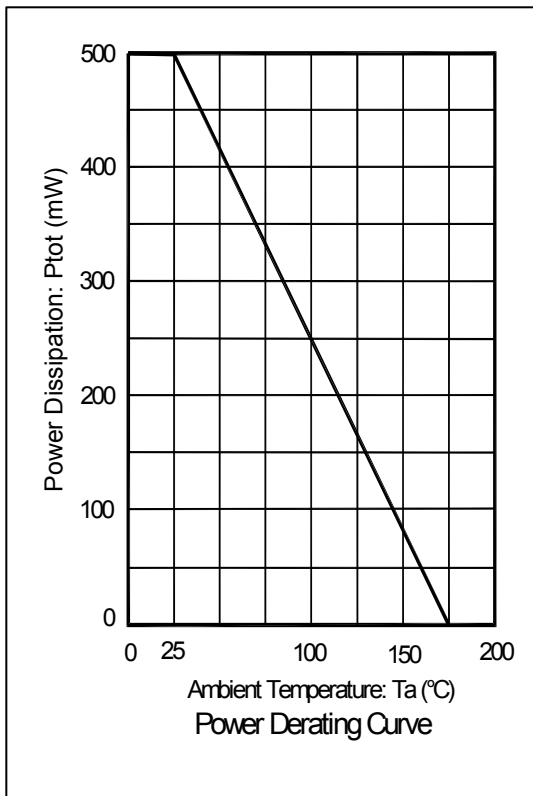
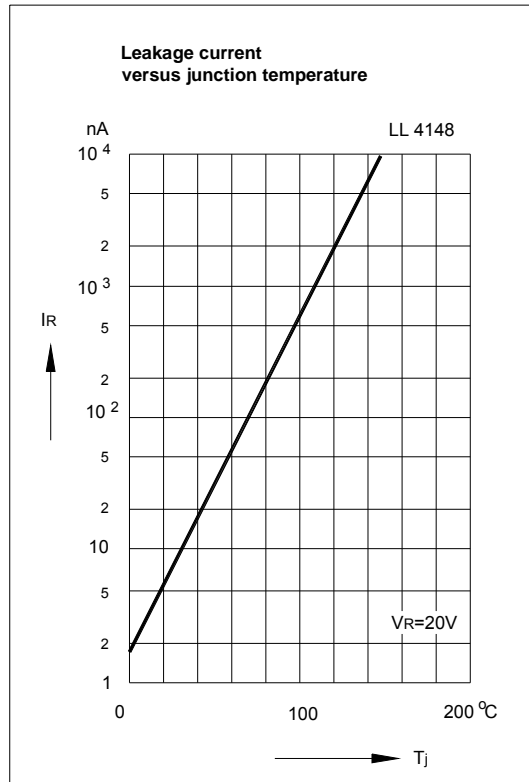
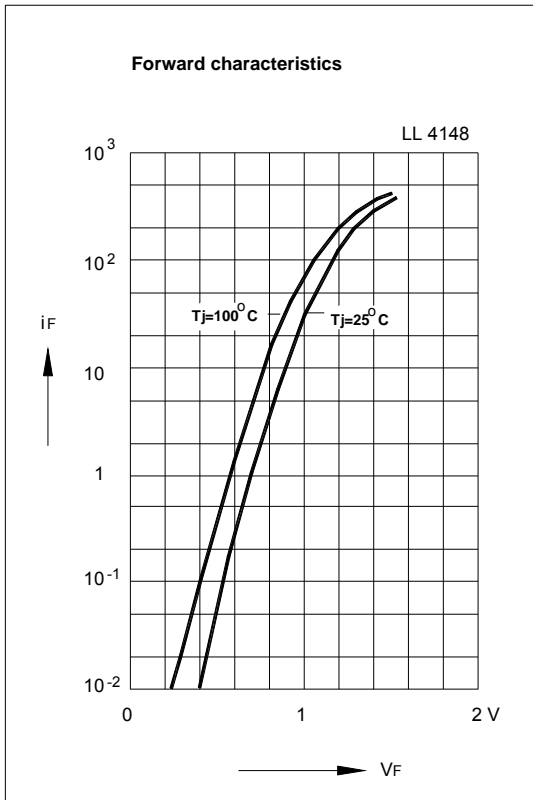
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5 1 4	A
		at $t = 1$ s	
		at $t = 1$ ms	
		at $t = 1$ μ s	
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage tested with 100 μ A Pulses	$V_{(BR)R}$	100	-	V
Forward Voltage at $I_F = 10$ mA	V_F	-	1	V
Leakage Current at $V_R = 20$ V	I_R	-	25	nA
at $V_R = 75$ V	I_R	-	5	μ A
at $V_R = 20$ V, $T_j = 150^\circ\text{C}$	I_R	-	50	μ A
Capacitance at $V_R = 0$, $f = 1$ MHz	C_{tot}	-	4	pF
Voltage Rise when Switching on tested with 50 mA Forward Pulses $t_p = 0.1$ s, Rise Time < 30 ns, $f_p = 5$ to 100 KHz	V_{fr}	-	2.5	V
Reverse Recovery Time at $I_F = 10$ mA, $I_R = 60$ mA, $I_{rr} = 0.1 \times I_R$	t_{rr}	-	4	ns





单击下面可查看定价，库存，交付和生命周期等信息

[>>ST\(先科\)](#)